

REMARKS

Claims 21-23 and 25-41 are pending, with claims 21, 30 and 36 being independent. Claims 1-20 were previously canceled and claim 24 has been canceled in this amendment. Claims 21 and 25 have been amended and claims 26-41 have been added. No new matter has been introduced.

Claims 21-23 and 25 have been rejected under section 112, second paragraph. Applicant requests reconsideration and withdrawal of this rejection in view of the amendments to independent claim 21.

Claims 21, 23 and 25 have been rejected as being unpatentable over Okada (U.S. Patent No. 5,582,640) in view of Kurihara (JP 08-211367). Applicant requests reconsideration and withdrawal of this rejection because neither Okada, Kurihara, nor any proper combination of the two describes or suggests a metal element contained in the semiconductor film for promoting crystallization; a layer comprising an element selected from the group consisting of titanium, tungsten, tantalum and molybdenum, and provided adjacent to at least one of the source region and the drain region with a silicide thereof therebetween; an interlayer insulating film provided over the semiconductor film and the gate electrode; and a contact hole provided in the interlayer insulating film, over at least one of the source region and the drain region, and over the layer comprising the element selected from the group consisting of titanium, tungsten, tantalum and molybdenum.

Claim 22 has been rejected as being unpatentable over Okada in view of Kurihara and Ukai (U.S. Patent No. 4,810,060). Applicant requests reconsideration and withdrawal of this rejection because Ukai does not remedy the failure of Okada and Kurihara to describe or suggest the subject matter of independent claim 21 from which claim 22 depends.

Claim 21 also has been rejected for obviousness-type double patenting over claim 5 of U.S. Patent No. 6,380,560. Applicant requests reconsideration and withdrawal of this rejection in view of the amendments to claim 21.

Claim 23 has been rejected for obviousness-type double patenting over claim 16 of U.S. Patent No. 6,730,932 in view of Clark. Applicant requests reconsideration and withdrawal of this rejection in view of the amendments to claim 21.

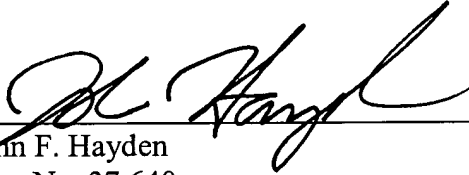
Similarly to claim 21, each of new independent claims 30 and 36 recites a metal element contained in the semiconductor film for promoting crystallization; a layer (claim 30) or an island pattern (claim 36) comprising an element selected from the group consisting of titanium, tungsten, tantalum and molybdenum, and provided adjacent to at least one of the source region and the drain region with a silicide thereof therebetween; an interlayer insulating film provided over the semiconductor film and the gate electrode; and a contact hole provided in the interlayer insulating film, over at least one of the source region and the drain region, and over the layer comprising the element selected from the group consisting of titanium, tungsten, tantalum and molybdenum. Accordingly, new claims 30-41 are believed to be allowable for at least the reasons discussed above.

Applicant submits that all claims are in condition for allowance. No fees are believed to be due. Please apply any charges or credits to deposit account 06-1050.

Respectfully submitted,

Date: _____

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